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(54) Title: MICROELECTRONIC PACKAGE CONTAINING SILICON PATCHES FOR HIGH DENSITY INTERCONNECTS, AND METHOD OF MANUFACTURING SAME

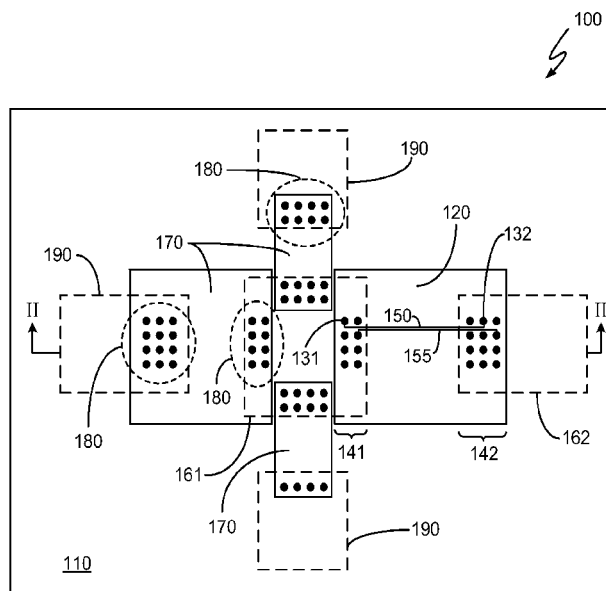


FIG. 1

(57) Abstract: A microelectronic package comprises a substrate (110), a silicon patch (120) embedded in the substrate, a first interconnect structure (131) at a first location of the silicon patch and a second interconnect structure (132) at a second location of the silicon patch, and an electrically conductive line (150) in the silicon patch connecting the first interconnect structure and the second interconnect structure to each other.



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